

METHOD OF PRODUCING SEMICONDUCTOR DEVICE

ABSTRACT

5 A method of producing a semiconductor device
capable of suppressing damages by corrosion on wiring in
a catalyst process performed in electroless plating
processing on a Co base material, etc. in producing a
semiconductor device having wiring of Cu, etc., having
10 steps of forming metal wiring including an additive on a
first insulation film formed in a semiconductor substrate,
and forming on the metal wiring a barrier layer for
preventing diffusion of constituting elements of the
metal wiring, wherein said additive is an element to
15 reduce corrosion of the metal wiring at the time of
forming the barrier layer in the step of forming the
metal wiring.